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(54) INSPECTING DEVICE OF PHOTODETECTOR

characteristic is measured.

(57) Abstract:

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PROBLEM TO BE SOLVED: To measure the photo-detecting characteristic of a photodetector in a wafer state semiconductor more simply and accurately by preparing a light source, a stage and a liquid crystal mask that changes the lighting region unrestrictedly in a dark box.

SOLUTION: A stage 8 that is arranged with a light source 2 and a stage 8 to mount a semiconductor wafer 7 is provided inside a dark box 1. To measure photo-detecting characteristic of a pellet that has a photodetector on a semiconductor wafer 7, a liquid crystal mask 3 that can change the lighting region unrestrictedly is provided. The semiconductor wafer 7, which has many photodetectors that are to be measured, is mounted on a movable stage 8 and metal contact probe 5 attached to a probe card 6 are touched to the electrodes of the photodetectors automatically. Light is radiated from a stabilized light source 2 with wavelength selecting functions, the main control system controls the liquid crystal mask 3 that is provided with a light permeating opening and closing window that radiates the light to any photodetecting surface and the photodetecting

